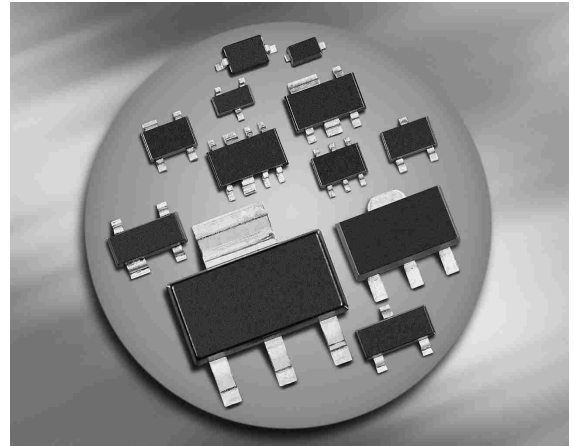
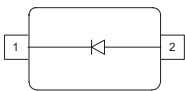


Silicon Tuning Diode

- For VHF 2-Band-hyperband-TV-tuners
- Very high capacitance ratio
- Low series resistance
- Excellent uniformity and matching due to "in-line" matching assembly procedure



BB669
BB689
BB689-02V



Type	Package	Configuration	L_S (nH)	Marking
BB669	SOD323	single	1.8	1
BB689	SCD80	single	0.6	EE
BB689-02V	SC79	Single	0.6	E

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	30	V
Peak reverse voltage ($R \leq 5\text{k}\Omega$)	V_{RM}	35	
Forward current	I_F	20	mA
Operating temperature range	T_{op}	-55 ... 150	°C
Storage temperature	T_{stg}	-55 ... 150	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current $V_R = 30\text{ V}$ $V_R = 30\text{ V}, T_A = 85^\circ\text{C}$	I_R	-	-	10 200	nA

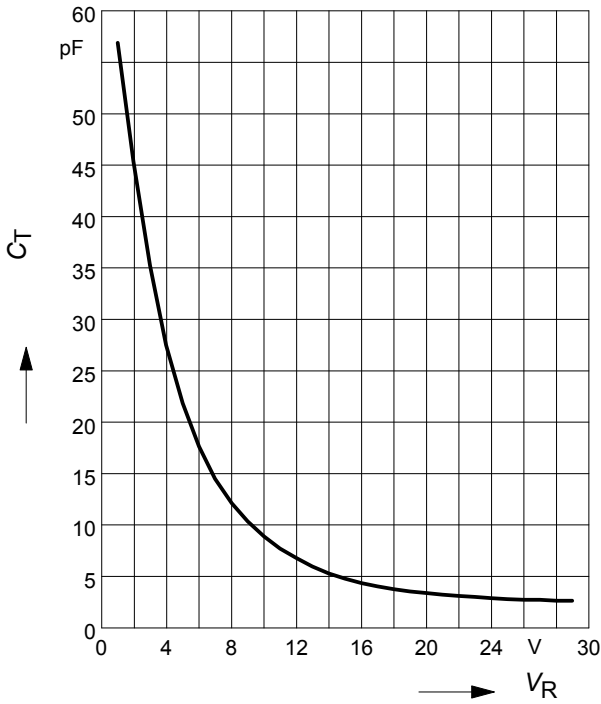
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Diode capacitance $V_R = 1\text{ V}, f = 1\text{ MHz}$ $V_R = 2\text{ V}, f = 1\text{ MHz}$ $V_R = 25\text{ V}, f = 1\text{ MHz}$ $V_R = 28\text{ V}, f = 1\text{ MHz}$	C_T	51 39.6 2.6 2.5	56.5 43.4 2.8 2.7	61.5 47.2 3 2.9	pF
Capacitance ratio $V_R = 1\text{ V}, V_R = 28\text{ V}, f = 1\text{ MHz}$	C_{T1}/C_{T28}	18	20.9	23.2	-
Capacitance ratio $V_R = 2\text{ V}, V_R = 25\text{ V}, f = 1\text{ MHz}$	C_{T2}/C_{T25}	14.5	15.5	17	
Capacitance matching ¹⁾ $V_R = 1\text{ V}, V_R = 28\text{ V}, f = 1\text{ MHz}$	$\Delta C_T/C_T$	-	-	2	%
Series resistance $V_R = 8\text{ V}, f = 470\text{ MHz}$	r_S	-	0.85	-	Ω

¹For details please refer to Application Note 047

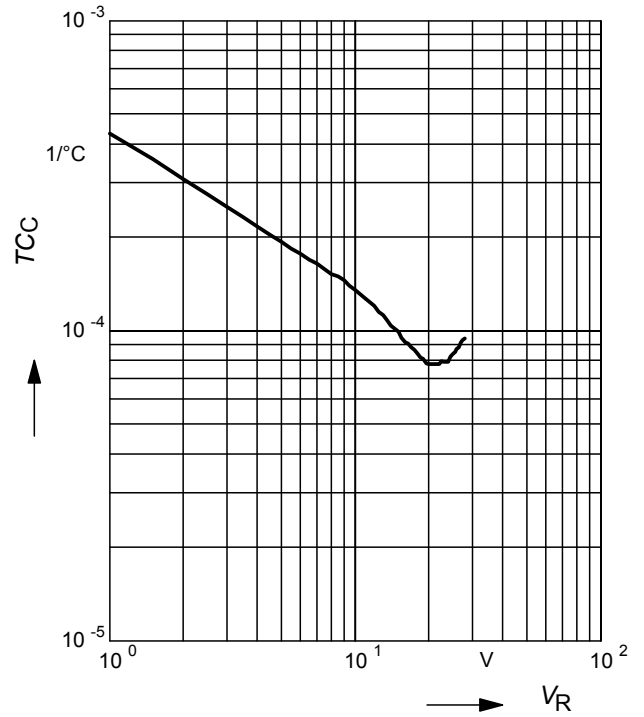
Diode capacitance $C_T = f(V_R)$

$f = 1\text{MHz}$



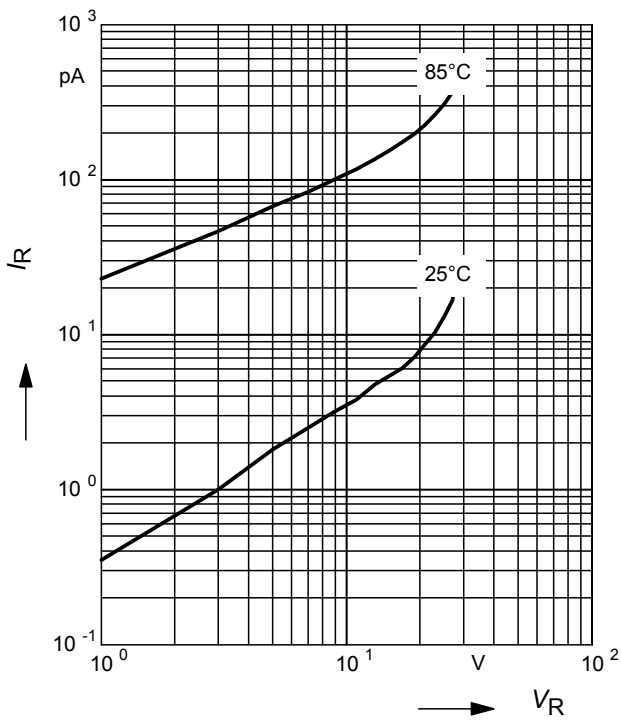
Temperature coefficient of the diode capacitance $T_{CC} = f(V_R)$

$T_{CC} = f(V_R)$



Reverse current $I_R = f(V_R)$

$T_A = \text{Parameter}$



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